CVD
Equipment
Corporation

firstnano

ET6000™ Horizontal Tube Furnace System

Next Generation Compact & Configurable Multi-Stack System for R&D and Pilot Production

ET6000™
Multi-Tube Horizontal Furnace System

Multi-Configurable Process Tubes

APCVD & LPCVD

High Temperature Processing Option up to 1400 °C

Precise Temperature Control ± 5 °C

50 Wafers per Tube; Supports 150 mm Substrates

Compact Footprint & Energy Efficient

The ET6000™ is ideal for a wide range of applications, each tube can be configured for thermal processes, including:

- **Wet/Dry Oxidation**
- **Atmospheric & Low Pressure Annealing**
- **Dopant Diffusion**
- **Polysilicon – Doped & Undoped**
- **Silicon Nitride – Stochiometric & Low Stress**
- **TEOS/PSG/BPSG**
- **LTO Silicon Dioxide – Doped & Undoped**
- **SiGe**

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enabling tomorrow's technologies™

ET6000™

CVD Equipment Corporation's ET6000™ multi-tube horizontal system is industry proven with over twenty years in the field, delivering batch wafer processing for advanced research and development environments. Our system supports up to four independently controlled process tubes, enabling simultaneous processing of up to fifty wafers per tube.

ET6000™ delivers precise temperature control for a wide variety of thermal processes. Advanced cascade temperature control allows for accurate internal temperature profiling and responsive external control for consistent thermal performance within each zone.

The ET6000™ is flexibly designed with individually configurable process tubes to support both atmospheric and low-pressure operations for versatile applications. This system features configurable precursor gas management and effluent gas abatement options are also available.

The ET6000™ is equipped to handle pyrophoric, corrosive, flammable, and toxic gases. The system integrates robust safety features, including visual and audible alarms, automated emergency response protocols, and comprehensive safety interlocks. These features ensure safe and reliable operation in demanding research settings.

Atmospheric Processing up to 1200 °C

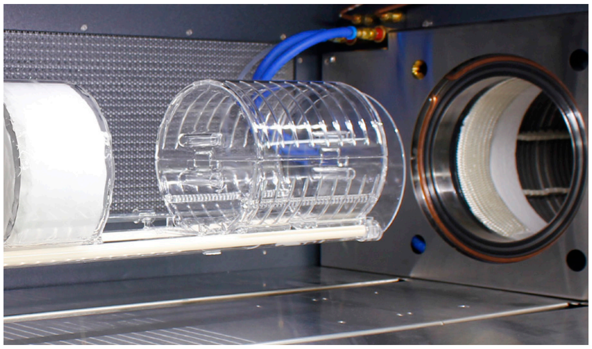
- Annealing
- Dopant Diffusion
- Wet/Dry Oxidation
- Quartz Process Tube

Optional High Temperature Processing up to 1400 °C

- Annealing
- Oxidation
- Atmospheric or Low Pressure
- Non-Quartz Process Tube

Low Pressure Processing up to 1100 °C

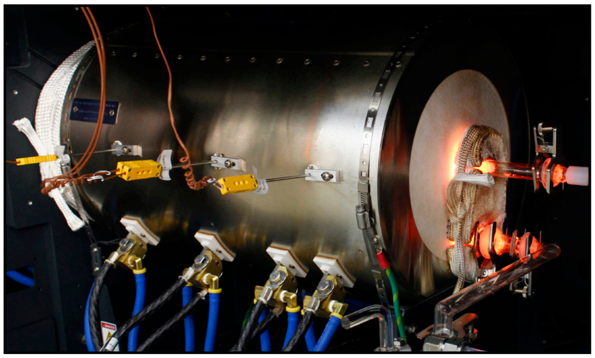
- Polysilicon – Doped & Undoped
- Silicon Nitride – Stochiometric & Low Stress
- SiGe
- TEOS/PSG/BPSG
- LTO Silicon Dioxide – Doped & Undoped
- Quartz Process Tube



Typical, up to fifty 100 mm or 150 mm Wafer Capacity

Typical Features and Options

- 3 zone resistive furnace with consistent thermal uniformity
- Proprietary cascade control for precise process temperature
- Up to four individually configurable process tubes
- Atmospheric and low-pressure process configurations
- Automatic cantilever substrate loading/unloading
- Up to 50 wafer capacity per process tube
- Differentially pumped double o-ring seals
- Mass flow controlled ultra-high purity gas lines
- CVDE proprietary Windows® based control software for real-time automatic process control and comprehensive documentation
- Compact footprint with energy-efficient design
- Remote monitoring capability
- In-situ oxide cleaning
- Optional exhaust gas conditioning system (not shown)



Multi Zone Furnace with Precise Temperature Control

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